Electronic structure and the Ferm is urface of ThRhIn₅ in comparison with uranium and transuranium compounds

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A bstract

By using a relativistic linear augmented-plane-wave method, we clarify energy band structure and the Ferm i surfaces of recently synthesized thorium compound $ThRhIn_5$. We not several cylindrical Ferm i surface sheets, which are similar to those of CeT In_5 (T=Ir and Co), $PuTGa_5$ (T=Co and Rh), and $AmCoGa_5$. We discuss such similarity among the compounds including rare-earth or actinide ions with dierent felectron numbers.

Keywords: Relativistic linear APW method, Ferm i surface, Thorium compounds PACS: 71.27 + a; 71.18 + y; 71.15 -m

In order to clarify 5f electron properties, it is useful to investigate thorium compounds both from experimental and theoretical view points, since it is possible to extract pure 5f-electron properties by subtracting the 5f contributions of thorium compounds from those of uranium and transuranium materials. In fact, the electronic structure of thorium compounds has been investigated by band theory as proper reference for the study of 5f electronic states of actinide compounds.

In this paper, we calculate energy band structure and Ferm i surface for ThRhIn5 [1] by applying a relativistic linear augmented plane wave (RLAPW) method. It belongs to the material group with HoCoGa5-type crystal structure, frequently referred to as \115". We compare the present result with those for Ce-[2], Pu-[3,4], and Am-115 compounds [5].

Here we calculate the energy band structure by using the RLAPW method with the exchange and correlation potential in the local density approximation. Them untinapproximation is adopted for the spatial shape of one-electron potential and self-consistent calculations are carried out for experimental lattice con-

stants. Note that all 5f electrons are assumed to be itinerant in our calculations. The energy band structure for ThRhIn5 is shown in Fig. 1. The Ferm i level, E_F, is located at 0.428 Ryd. and shown by a solid line in Fig. 1. Since 13th, 14th, 15th, and 16th bands are partially occupied, these four bands construct the Ferm i surface. The number of the valence electrons in the APW sphere is partitioned according to the sites and the angularm om enta is as 0.42 (s), 6.13 (p), 2.41 (d) and 0.55(f) in the Th sphere. There are 8.74 valence electrons outside the APW sphere in the prim it ive cell. Here we note a signi cant amount of f component due to large hybridization between 5f and 5p electron states. The value of the f component is a little larger than that of fcc-Th, obtained by the RAPW calculation [6], in which the value of 0.41 was reported for the f component. The density of states (DOS) at $E_{\rm F}$ is evaluated as 56.6 states/Ryd.cell. The contribution from the f states to the DOS at $E_{\rm F}$ amounts to 14.8% of the total. Above E_F near the M point, at 5f bands split into two groups, speci ed by j=5/2 for lower and 7/2 for upper bands, respectively, where j is the total angularm om entum . The magnitude of the splitting in 5f states corresponds to the spin-orbit coupling, estim ated as 0.048 Ryd. As shown in Fig. 1, them ain part

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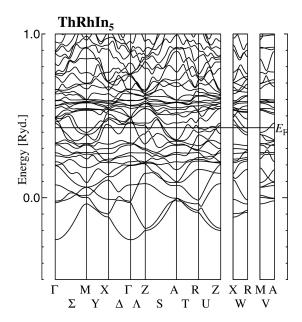


Fig. 1. Energy band structure of ThRhIn $_5$ calculated by the RLAPW method.E $_{\rm F}$ indicate the position of the Ferm i level.

of the f bands exist just above E $_{\text{F}}$.

In Fig. 2, we show the Fermi surfaces of $ThRhIn_5$. The Ferm isurfaces from the 13th band have one sheet centered at the point, two equivalent sheets centered at the X points. The 14th band constructs a large cylindrical hole sheet centered at the point, which exhibits a complex network consisting of big \arm s" along the edges of the Brillouin zone, as observed in Fig. 2(b). The 15th band has a cylindrical electron sheet centered at the M point. The Ferm isurface from the 16th band consists of one hole sheet centered at the M point. The number of carriers contained in these Ferm i-surface sheets are 0.051 holes/cell, 0.603 holes/cell, 0.581 electrons/cell, and 0.073 electrons/cell in the 13th, 14th, 15th, and 16th bands, respectively. The total number of holes is equal to that of electrons, since ThRhIn5 is a compensated metal.

We rem ark that the Ferm isurfaces of ThRhIn $_5$ look sim ilar to those of CeT In $_5$ (T = Ir and Co) [2], PuTG a $_5$ (T = Co and Rh) [3,4], and Am CoG a $_5$ [5]. If we assume the trivalent rare-earth or actinide ion in 115 structure, we nd zero, one, ve, and six electrons per ion for Th-Ce-, Pu-, and Am-115 com pounds, respectively. In the j-j coupling scheme, we accomm odate n electrons in the j=5/2 sextet and thus, the electron-hole relation is expected [7]. In this sense, it seems to be natural to observe similar Ferm i-surface structure for the cases of n and 6 n electrons. Namely, it is enough to discuss the similarity between the cases of n=0 and 1. The Ferm i surfaces of ThRhIn $_5$ constructed from the four bands contain the f components appreciably due to the large hybridization between f and p electrons near

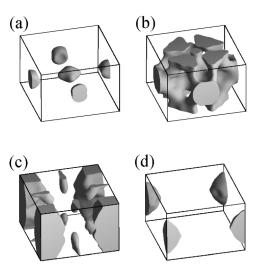


Fig.2.C alculated Ferm isurfaces of ThRhIn $_5$ for (a) 13th band hole sheets, (b) 14th band hole sheets, (c) 15th band electron sheets, and (d) 16th band electron sheets.N ote that the center of the B rillouin zone is the point.

the Ferm i level. In fact, in our band-calculation results, we have found $0.55\ 5f$ electrons in T h atom .Then, the Ferm i-surface structure of T h-115 becomes similar to that of Ce-115.

In sum m ary, we have perform ed the band calculation for ThRhIn $_5$ by using the RLAPW m ethod. The sim ilarity in the Ferm i-surface structure among Th-, Ce-, Pu-, and Am-115 compounds are understood by the electron-hole relation in the j-j coupling scheme and the large hybridization between f-and 5p-electron states in the vicinity of E $_{\rm F}$.

We thank Y. Haga, K. Kubo, T. D. Matsuda, H. Onishi, Y. Onuki, K. Ueda, H. Yamagami, and H. Yasuoka for discussions. One of the authors (T. H.) is supported by Japan Society for the Promotion of Science and by the Ministry of Education, Culture, Sports, Science, and Technology of Japan. The computation of this work has been done using the facilities of Japan Atomic Energy Research Institute.

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